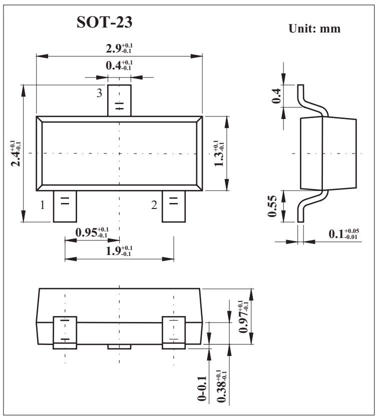
Silicon Schottky Barrier Diode

HRW0503A

Features

- Low forward voltage drop and suitable for high effifiency rectifying.
- MPAK package is suittable for high density surface mounting and high speed assembly.



Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	30	V
Average rectified current	I_O	500	mA
Non-repetitive peak forward surge current	I_{FSM} (Note 1)	5	A
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to + 125	℃

Note

1. 50Hz sine wave 1 pulse

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	I_F = 500 mA			0.55	V
Reverse current	I_R	V_R = 30 V			50	μ A
Capacitance	C	V_R = 0 V, f = 1MHz		65		pF

Marking

Marking	S6